
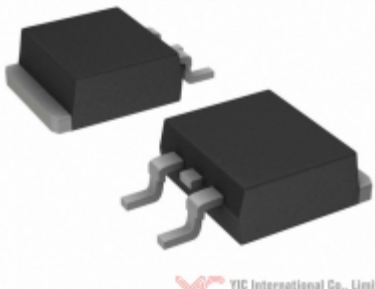
	<p>FQB11P06TM</p>
	<p>Hersteller-Teilenummer: FQB11P06TM</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET P-CH 60V 11.4A D2PAK</p> <p>Datenblätter:  FQB11P06TM.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 2435 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQB11P06TM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET P-CH 60V 11.4A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	2435 pcs Stock
Hersteller Standard Vorlaufzeit	6 Weeks
detaillierte Beschreibung	P-Channel 60V 11.4A (Tc) 3.13W (Ta), 53W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 175°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 53W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	60V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	11.4A (Tc)
Rds On (Max) @ Id, Vgs	175 mOhm @ 5.7A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	17nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	550pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±25V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	FQB11P06TM-ND



















































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 <p>FQB11P06TM**CN-SCI RHFAIRCHI FQB11P06TM**CN-SCI RHFAIRCHI</p>	 <p>FQB11N40TM Fairchild/ON Semiconductor MOSFET N-CH 400V 11.4A D2PAK</p>	 <p>FQB11N60TM FAIRCHILD FQB11N60TM FAIRCHILD</p>	 <p>FQB11P06TM Fairchild/ON Semiconductor MOSFET P-CH 60V 11.4A D2PAK</p>
 <p>FQB12N20L Fairchild/ON Semiconductor FQB12N20L FAIRCHILD</p>	 <p>FQB12N50 FAIRCHILD FQB12N50 FAIRCHILD</p>	 <p>FQB12N50TM Original FQB12N50TM Original</p>	 <p>FQB11N60FTM FAIRCHILD FQB11N60FTM FAIRCHILD</p>

heiße Teile

Mehr

 FQB10N20C	 FQB10N20CTM	 FQB10N20CTM	 FQB10N20L	 FQB10N20LTM
 FQB10N20LTM	 FQB10N20TM	 FQB10N20TM	 FQB10N50CF	 FQB10N50CFTM
 FQB10N50CFTM_WS	 FQB10N60C	 FQB10N60CTM	 FQB10N60CTM	 FQB11N40
 FQB11N40C	 FQB11N40CTM	 FQB11N40CTM	 FQB11N60FTM	 FQB11N60TM
 FQB11P06	 FQB11P06TM	 FQB11P06TM**CN-SCI	 FQB12N50TM	 FQB12N50TM_AM002
 FQB12N50TM_AM002	 FQB12N60	 FQB12N60C	 FQB12N60CTM	 FQB12N60CTM
 FQB12N60TM	 FQB12N60TM_AM002	 FQB12N60TM_AM002	 FQB12P10	 FQB12P10TM
 FQB12P10TM	 FQB12P20	 FQB12P20TM	 FQB12P20TM	 FQB13N06L
 FQB13N10	 FQB13N10L	 FQB13N50	 FQB13N50CTM	 FQB13N50CTM
 FQB140N03L	 FQB14N30TM	 FQB14N30TM	 FQB16N25TM	 FQB16N25TM

Contact us:Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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